

Description:

This N+P Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

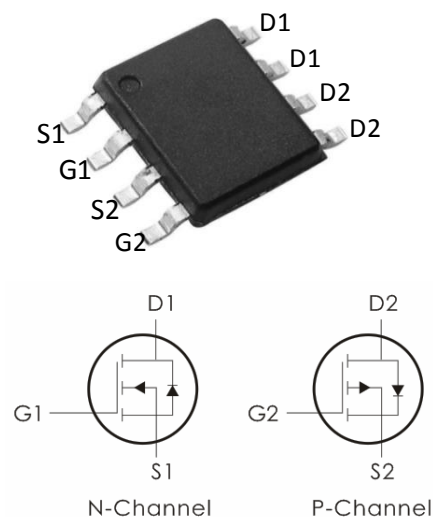
Features:

N-Channel: $V_{DS}=40V, I_D=8A, R_{DS(on)} < 25m\Omega @ V_{GS}=10V$ (Typ: $17m\Omega$)

P-Channel: $V_{DS}=-40V, I_D=-7.2A, R_{DS(on)} < 40m\Omega @ V_{GS}=-10V$ (Typ: $29m\Omega$)

- 1) Low gate charge.
- 2) Green device available.
- 3) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 4) Excellent package for good heat dissipation.

5 MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOS4614H	S4614H	SOP-8	3000 pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	N-Channel	P-Channel	Units
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
I_D	Continuous Drain Current- $T_A=25^\circ C$ ¹	8	-7.2	A
	Continuous Drain Current- $T_A=100^\circ C$ ¹	5.6	-5	
I_{DM}	Pulsed Drain Current ²	32	-28.8	A
E_{AS}	Single pulse avalanche energy ³	110	25	mJ
P_D	Power Dissipation - $T_A=25^\circ C$	2	1.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ C$

Thermal Characteristics:

Symbol	Parameter	N-CH	P-CH	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	76	$^\circ C/W$

N-Channel Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	40	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =40V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1	---	2.2	V
R _{DS(on)}	Drain-Source On Resistance ⁴	V _{GS} =10V, I _D =8A	---	17	25	m Ω
		V _{GS} =4.5V, I _D =5A	---	25	35	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1MHz	---	800	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	55	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =20V, I _D =10A, R _{ENG} =2.5 Ω ,V _{GS} =10V	---	4	---	ns
t _r	Rise Time		---	3	---	ns
t _{d(off)}	Turn-Off Delay Time		---	15	---	ns
t _f	Fall Time		---	2	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =20V, I _D =10A	---	12	---	nC
Q _{gs}	Gate-Source Charge		---	3.2	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	3.1	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =2.5A	---	---	1.2	V
I _S	Continuous Drain Curren	V _D =V _G =0V	---	---	8	A
I _{SM}	Pulsed Drain Current		---	---	32	A

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C$, $V_{DD}=20V$, $V_G=10V$, $L=0.5mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

N-Typical Characteristics: ($T_A=25^{\circ}C$ unless otherwise noted)

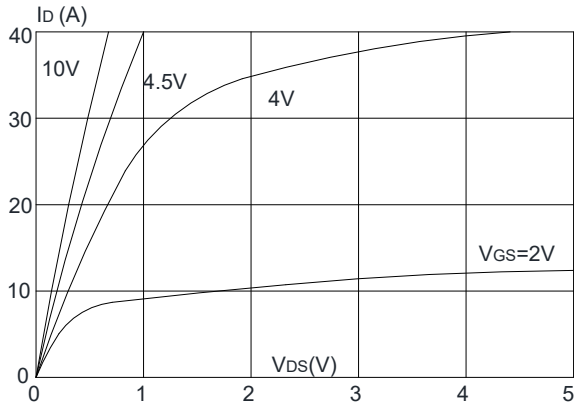


Figure 1: Output Characteristics

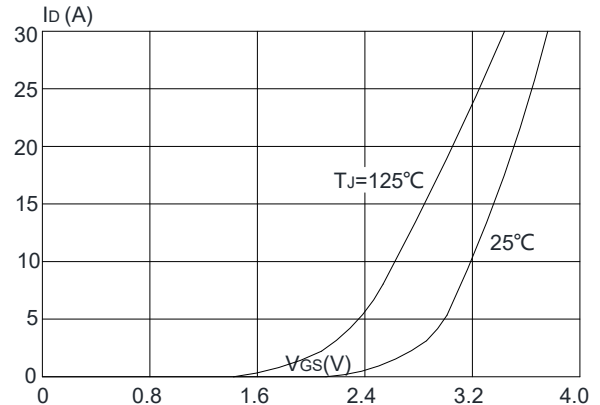


Figure 2: Typical Transfer Characteristics

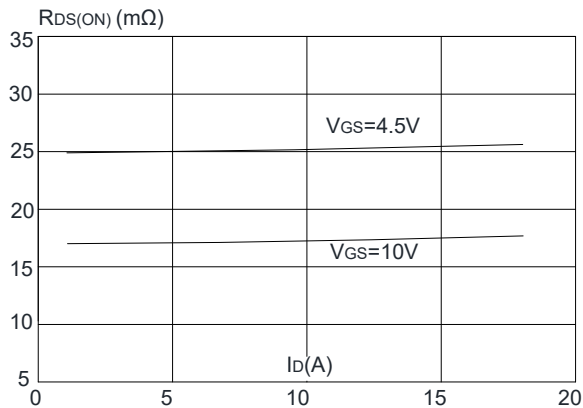


Figure 3: On-resistance vs. Drain Current

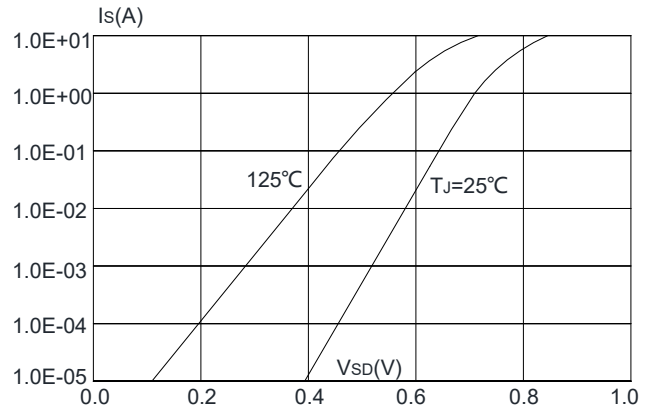


Figure 4: Body Diode Characteristics

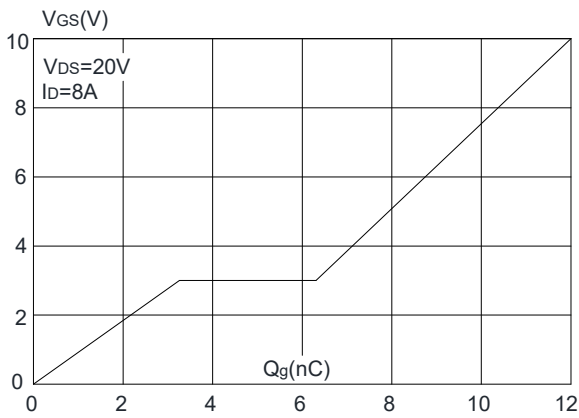


Figure 5: Gate Charge Characteristics

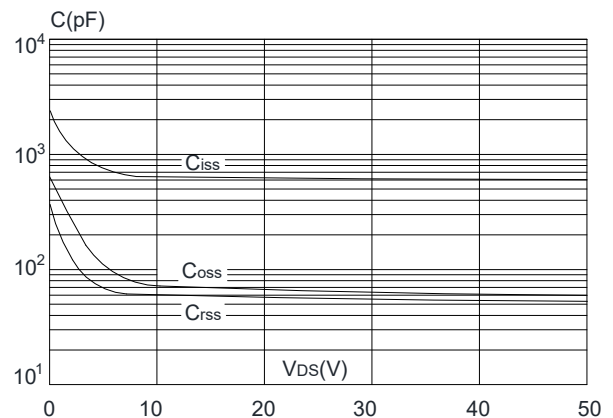


Figure 6: Capacitance Characteristics

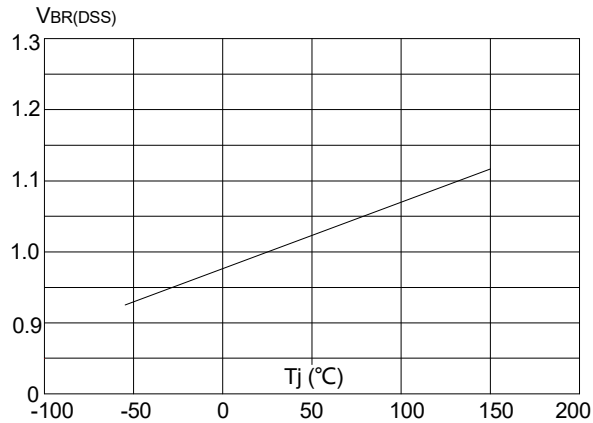


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

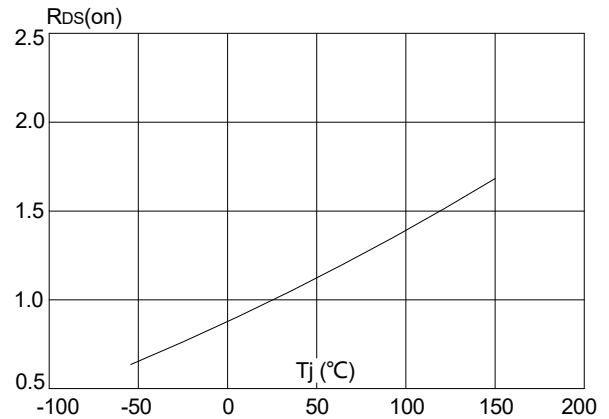


Figure 8: Normalized on Resistance vs. Junction Temperature

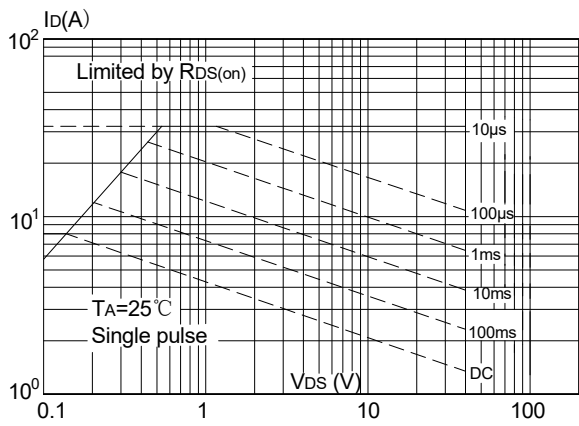


Figure 9: Maximum Safe Operating Area

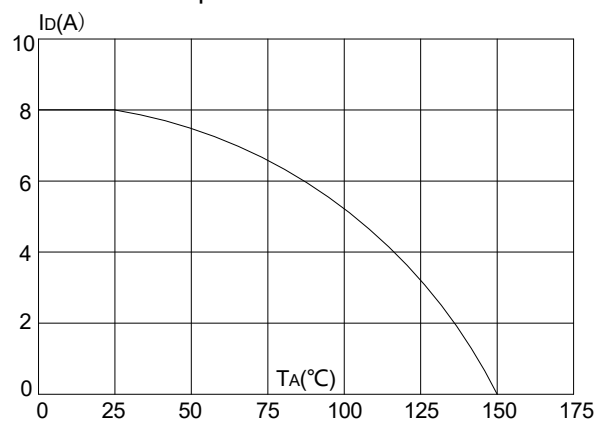


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

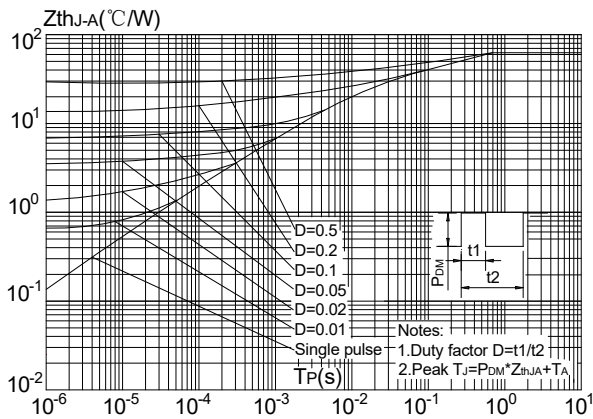


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

P-Channel Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-40	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-40V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance ⁴	V _{GS} =-10V, I _D =-6A	---	29	40	m Ω
		V _{GS} =-4.5V, I _D =-4A	---	35	45	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	1000	---	pF
C _{Oss}	Output Capacitance		---	101	---	
C _{rss}	Reverse Transfer Capacitance		---	84	---	
Switching Characteristics ⁴						
t _{d(on)}	Turn-On Delay Time	V _{DD} = -20V, I _D =-5A V _{GS} = -10V, R _{GEN} =3 Ω	---	5	---	ns
t _r	Rise Time		---	2	---	ns
t _{d(off)}	Turn-Off Delay Time		---	53	---	ns
t _f	Fall Time		---	30	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-20V, I _D =-5A	---	23	---	nC
Q _{gs}	Gate-Source Charge		---	4	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	4	---	nC
Drain-Source Diode Characteristics						
I _S	Continuous Drain to Source Diode	V _D =V _G =0V	---	---	-7.2	A
I _{SM}	Pulsed Drain to Source Diode		---	---	-28.8	---
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =-6A	---	---	-1.2	V
T _{rr}	Reverse Recovery Time	I _F =-5A, T _J =25 °C	---	13	---	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/us	---	7	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C$, $V_{DD}=-20V$, $V_G=-10V$, $L=0.5mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

P-Typical Characteristics: ($T_A=25^{\circ}C$ unless otherwise noted)

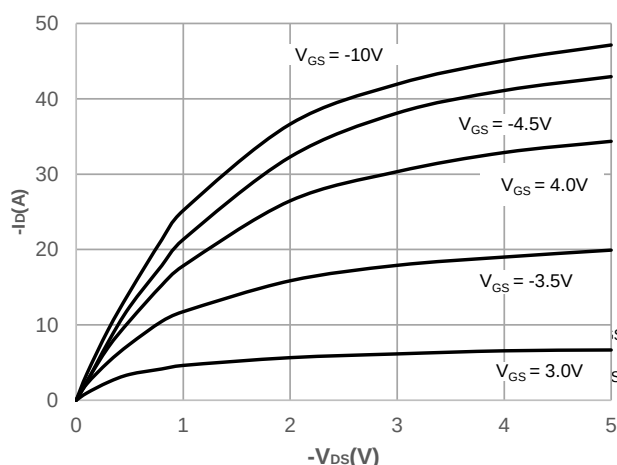


Figure 1: Output Characteristics

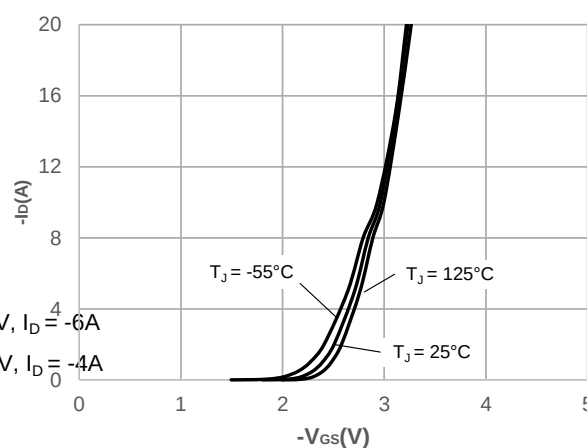


Figure 2: Typical Transfer Characteristics

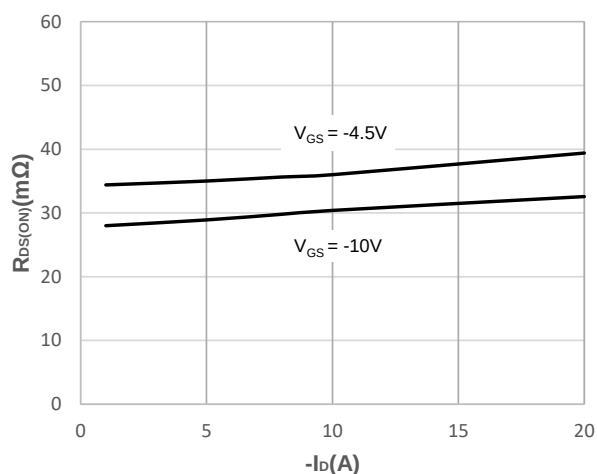


Figure 3: On-resistance vs. Drain Current

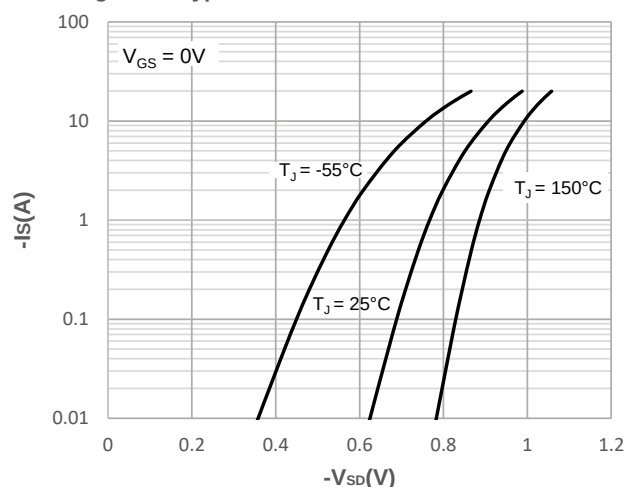


Figure 4: Body Diode Characteristics

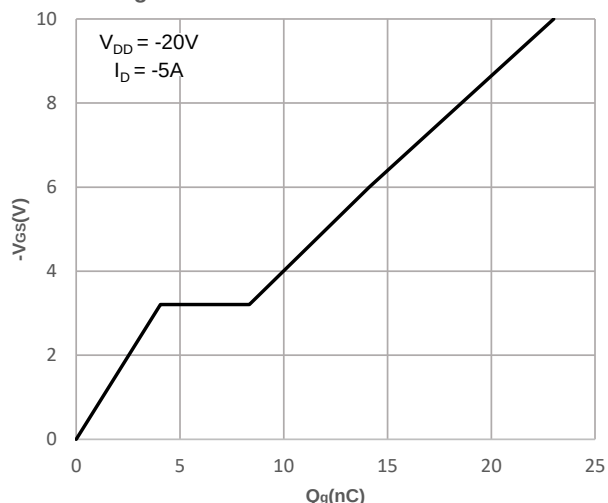


Figure 5: Gate Charge Characteristics

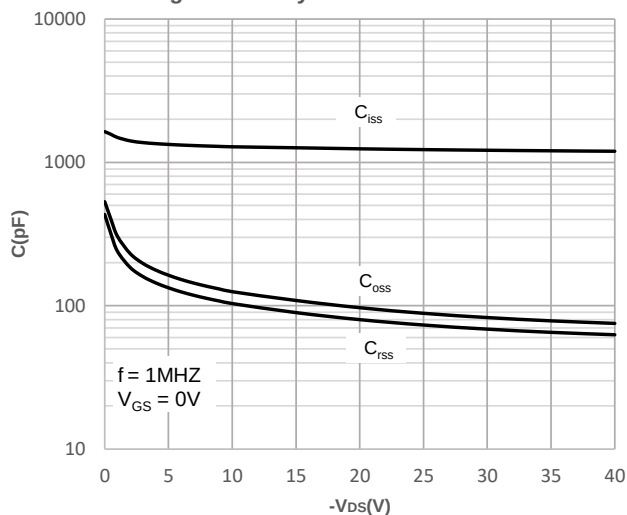


Figure 6: Capacitance Characteristics

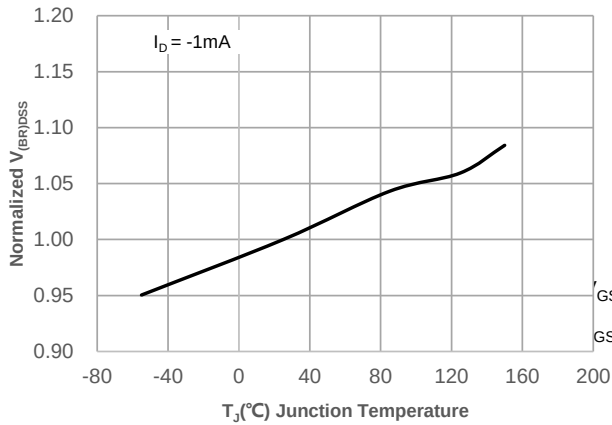


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

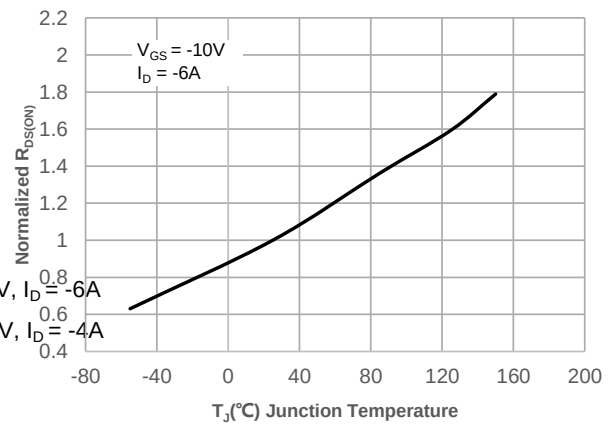


Figure 8: Normalized on Resistance vs. Junction Temperature

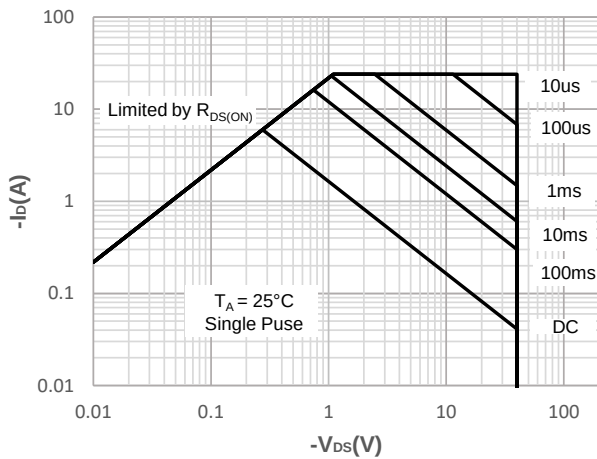


Figure 9: Maximum Safe Operating Area

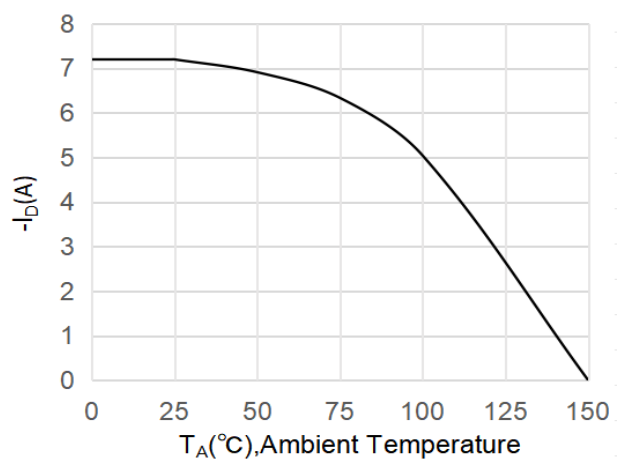


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

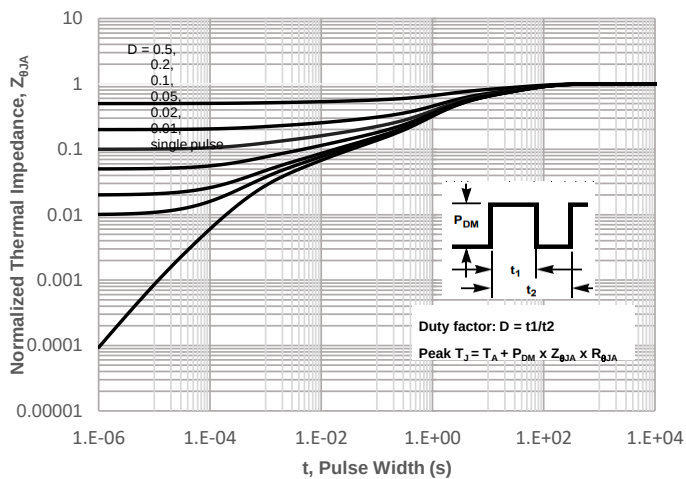


Figure 11: Normalized Maximum Transient Thermal Impedance

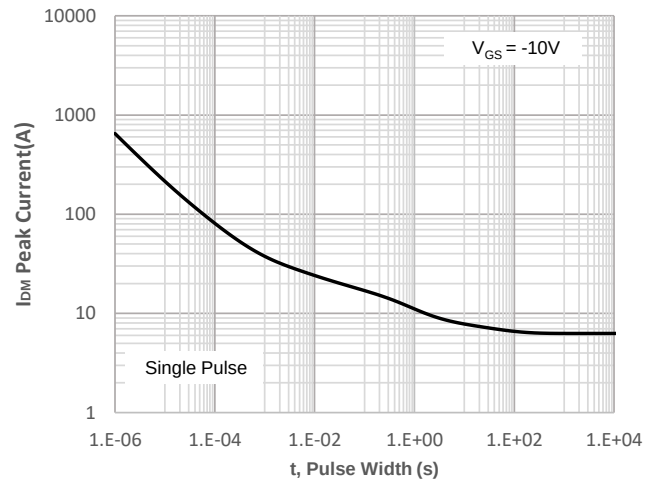
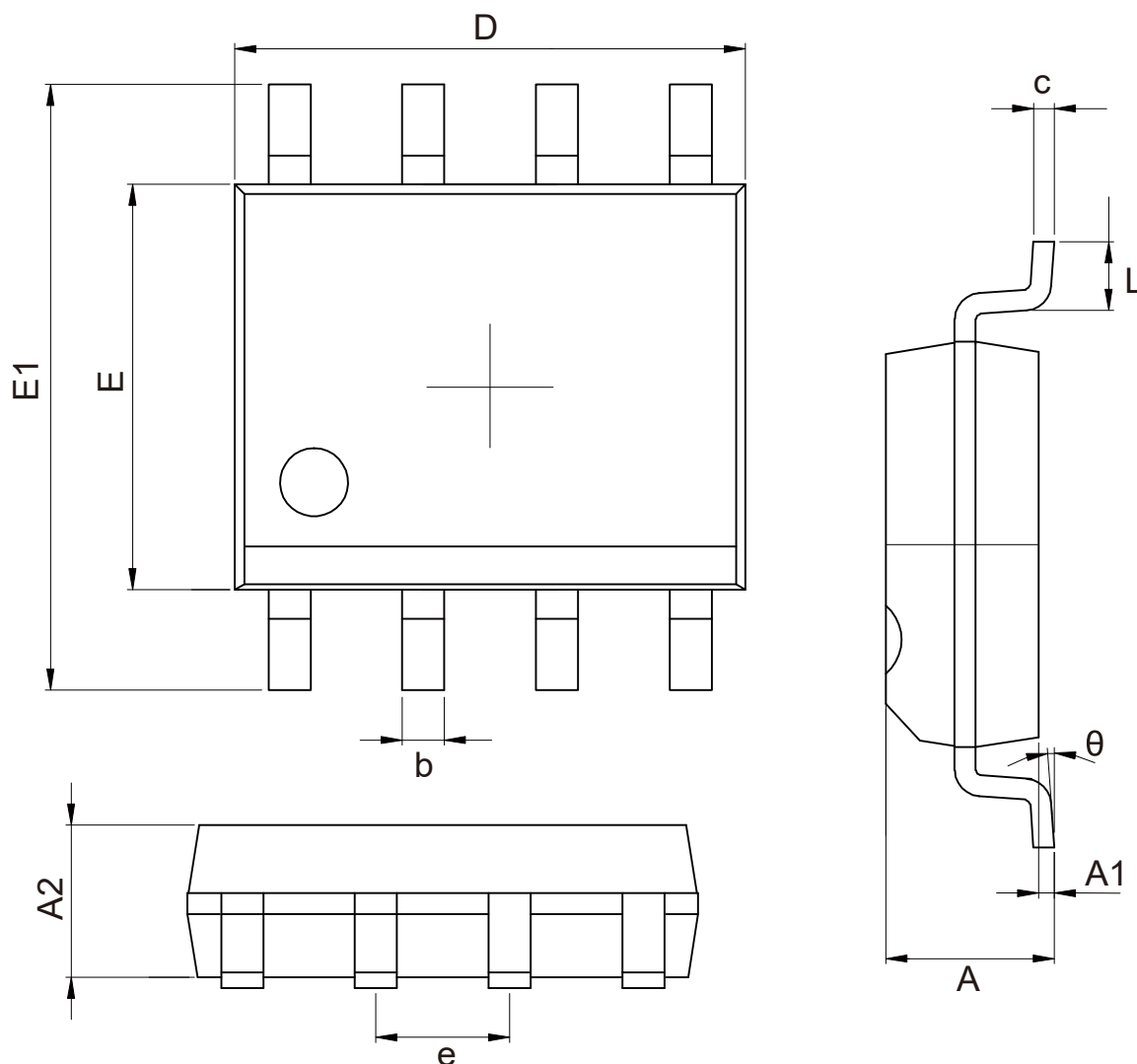


Figure 12: Peak Current Capacity

SOP-8D Package Information:

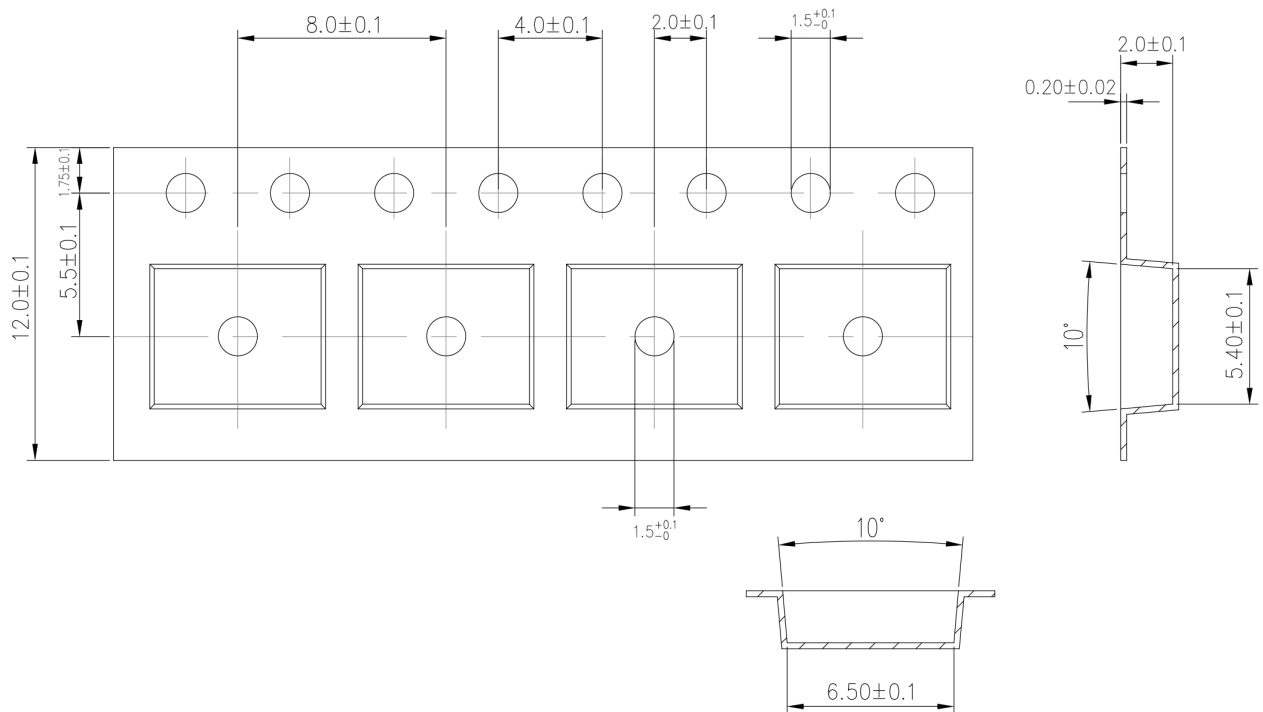
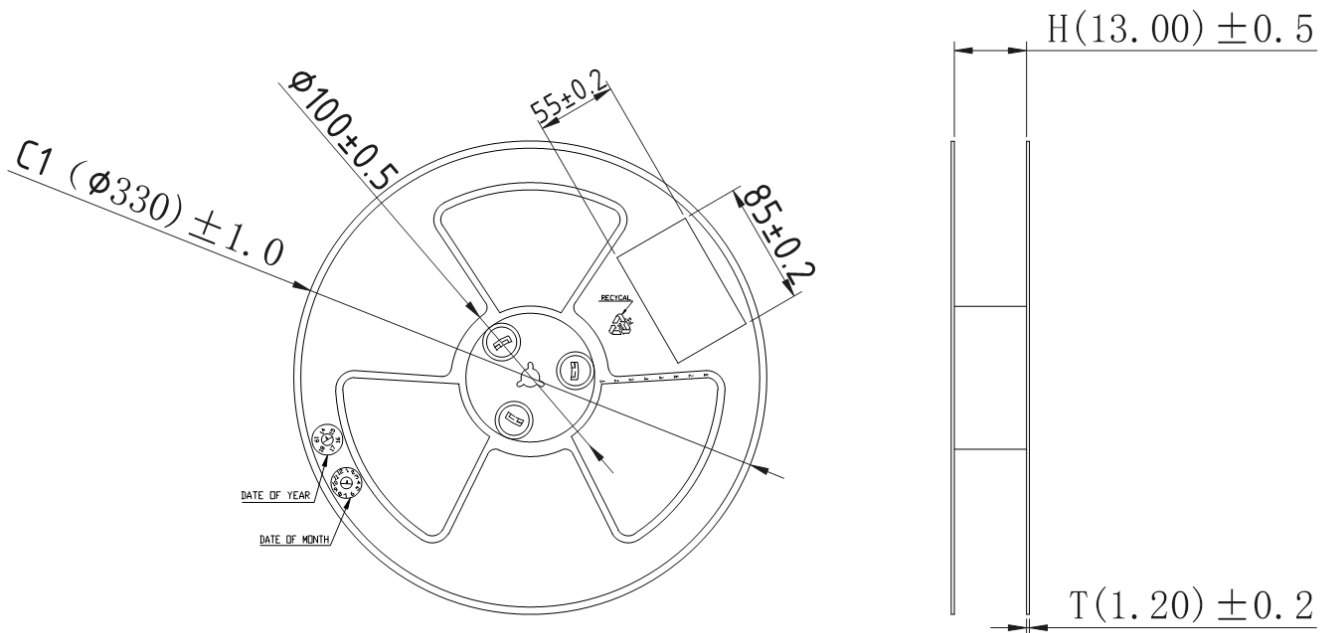


COMMON DIMENSIONS			
CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	1.350	—	1.750
A1	0.100	—	0.250
A2	1.350	—	1.550
b	0.330	—	0.510
c	0.170	—	0.250
D	4.700	—	5.100
E	3.800	3.900	4.000
E1	5.800	—	6.200
e	1.270BSC		
L	0.400	—	1.270
θ	0°	—	8°

Unit:mm

Tape & Reel Information

Dimensions in mm



Pulling direction →

Marking Information:

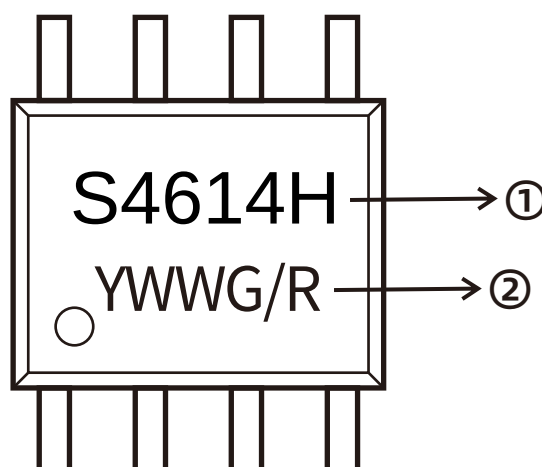
①. Part NO.

②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
2.1	2026-04-22	Release of final version

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